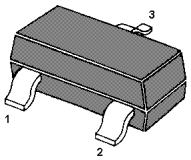
1SS226

Features:

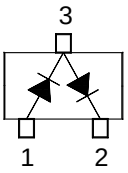
- ☐ Small package
- ☐ Low forward voltage
- ☐ Fast reverse recovery time
- ☐ Small total capacitance

SOT-23

RoHS COMPLIANT



Marking:C3



Absolute Maximum Ratings (T_a = 25 °C)

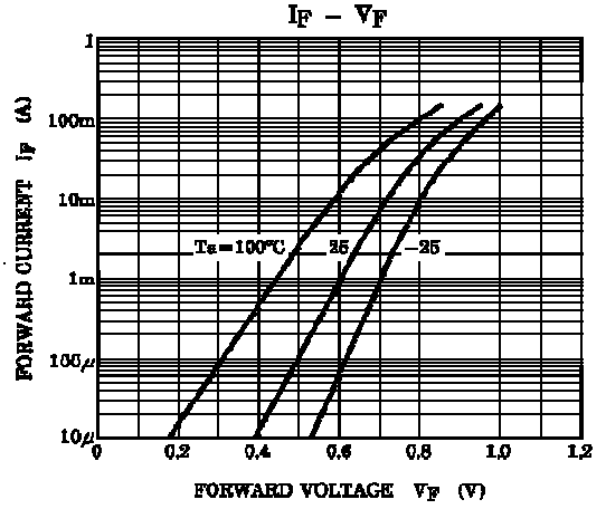
Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current (10 ms)	I_{FSM}	2	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

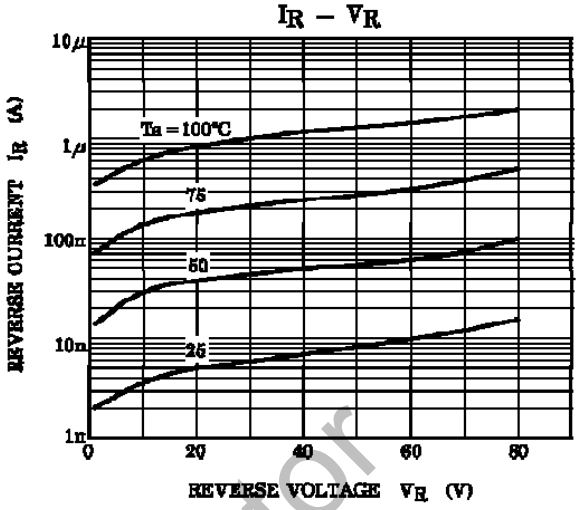
Characteristics at T_a = 25 °C

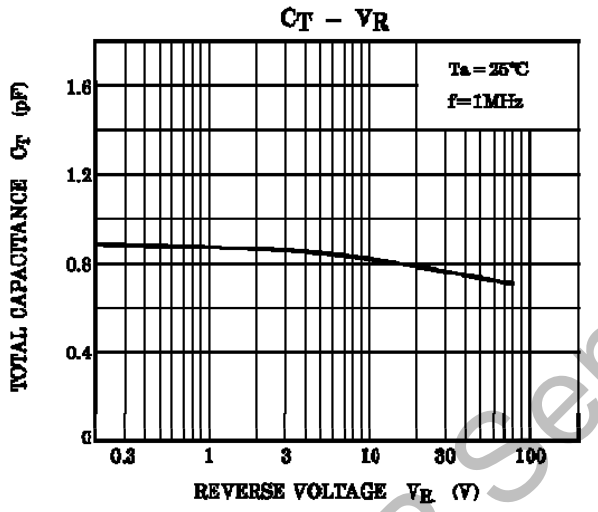
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	1.2	V
Reverse Current at V_R = 80 V	I_R	0.5	μA
Total Capacitance at V_R = 0 , f = 1 MHz	C_T	3	pF
Reverse Recovery Time at I_F = 10 mA	t_{rr}	4	ns

KTP Semiconductor

Typical Characteristics







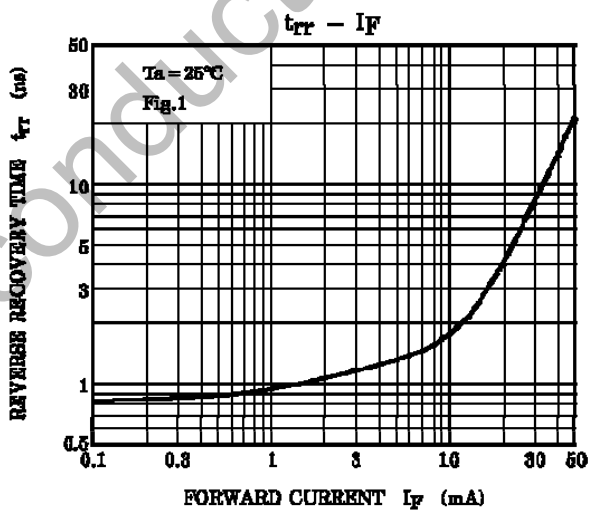
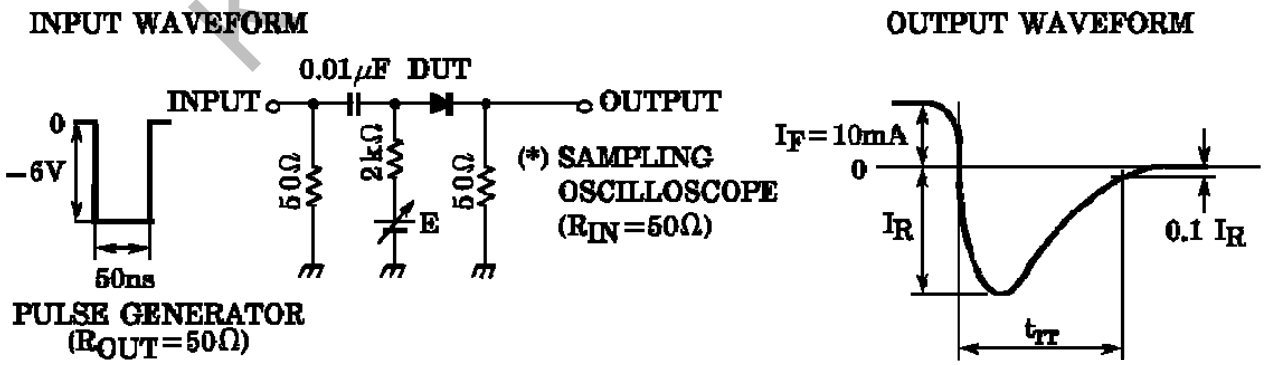


Fig.1 Reverse recovery time (t_{rr}) test circuit

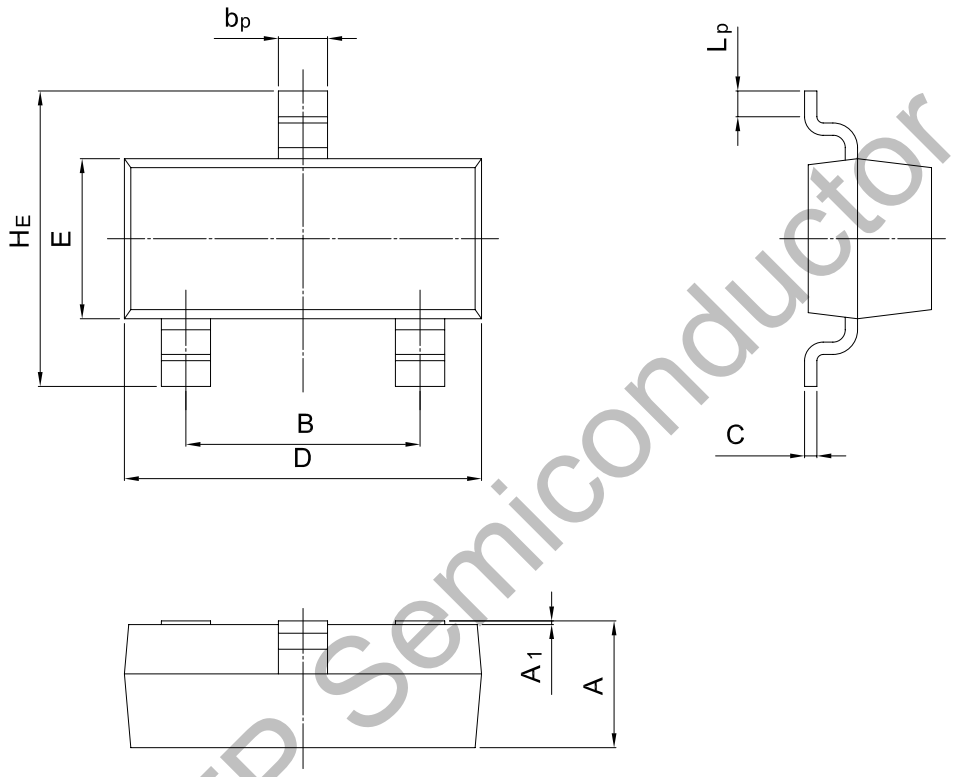


KTP Semiconductor

Package Dimension

SOT-23

Unit: mm



KTP Semiconductor

UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20